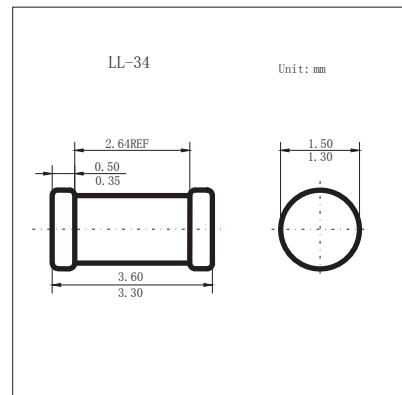


Switching Diodes

KLL4148

■ Features

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- General Purpose Rectification
- Silicon Epitaxial Planar Construction



■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	100	V
Reverse voltage	V_R	75	
Peak forward surge current ($t_p = 1 \mu\text{s}$)	I_{FSM}	2	A
Repetitive peak forward current	I_{FRM}	500	
Forward continuous current	I_F	300	mA
Average forward current	$I_{F(AV)}$	150	
Thermal resistance junction to ambient air ^{*1}	$R_{\theta JA}$	300	°C/W
Power dissipation ^{*1}	P_{tot}	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to 150	

* 1 Valid provided that electrodes are kept at ambient temperature

■ Electrical Characteristics ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R=100\mu\text{A}$	100			V
Forward voltage	V_F	$I_F=1\text{mA}$			0.715	
		$I_F=10\text{mA}$			0.855	
		$I_F=50\text{mA}$			1	
		$I_F=150\text{mA}$			1.25	
Reverse voltage leakage current	I_R	$V_R=20\text{V}$			25	nA
		$V_R=75\text{V}$			1	μA
Junction capacitance	C_j	$V_R=4\text{V}, f=1\text{MHz}$			4	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=0.1 \times I_R, R_L=100\Omega$			4	ns

Switching Diodes**KLL4148**

■ Typical Characteristics

